

SEMICONDUCTOR TM

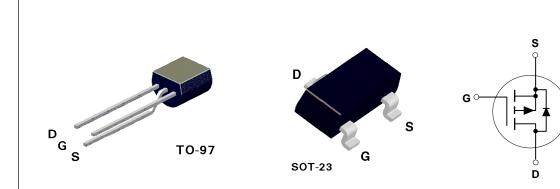
BSS84 / BSS110 P-Channel Enhancement Mode Field Effect Transistor

General Description

These P-Channel enhancement mode power field effect transistors are produced using Fairchild's proprietary, high cell density, DMOS technology. This very high density process is designed to minimize on-state resistance, provide rugged and reliable performance and fast switching. They can be used, with a minimum of effort, in most applications requiring up to 0.17A DC and can deliver pulsed currents up to 0.68A. This product is particularly suited to low voltage applications requiring a low current high side switch.

Features

- BSS84: -0.13A, -50V. R_{DS(ON)} = 10Ω @ V_{GS} = -5V.
 BSS110: -0.17A, -50V. R_{DS(ON)} = 10Ω @ V_{GS} = -10V
- Voltage controlled p-channel small signal switch.
- High density cell design for low R_{DS(ON)}.
- High saturation current.



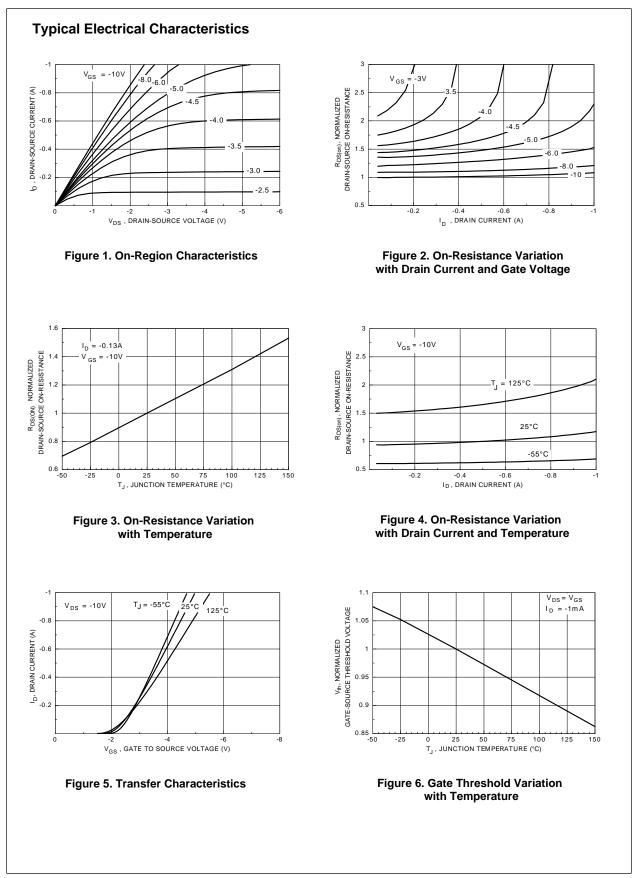
Absolute Maximum Ratings T_A = 25°C unless otherwise noted

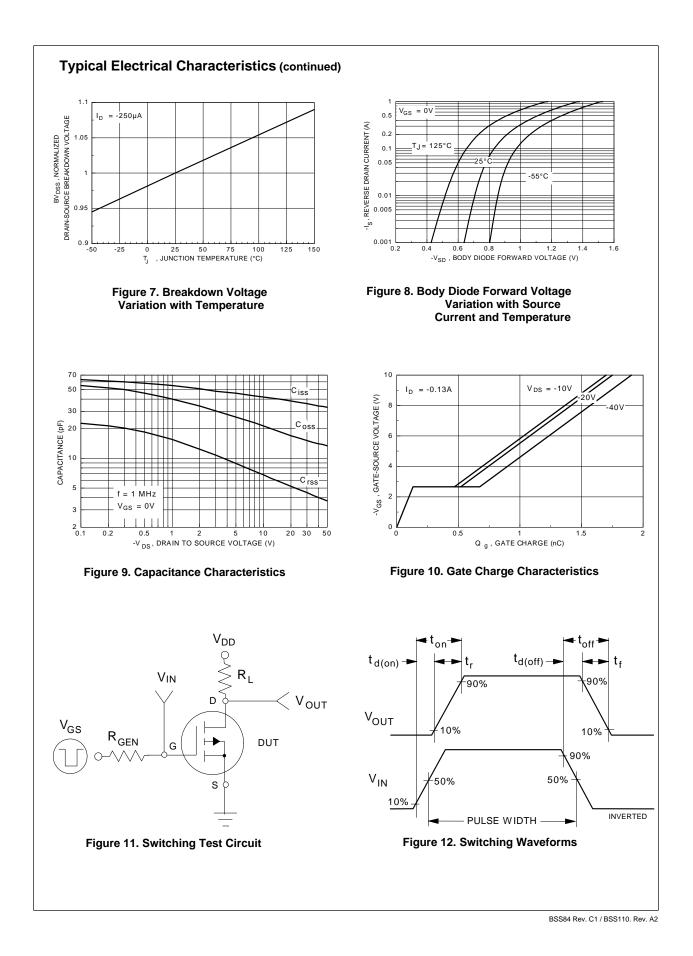
Symbol	Parameter	BSS84	BSS110	Units
V _{DSS}	Drain-Source Voltage	-50		V
V _{DGR}	Drain-Gate Voltage ($R_{GS} \le 20 \text{ K}\Omega$)	-50		V
V _{GSS}	Gate-Source Voltage - Continuous	±20		
I _D	Drain Current - Continuous @ $T_A = 30/35^{\circ}C$	-0.13	-0.17	А
	- Pulsed @ $T_A = 25^{\circ}C$	-0.52	-0.68	
P _D	Maximum Power Dissipation $T_A = 25^{\circ}C$	0.36	0.63	W
T_,T _{STG}	Operating and Storage Temperature Range	-55 to 150 °		
TL	Maximum lead temperature for soldering purposes, 1/16" from case for 10 seconds	300		
THERMA	L CHARACTERISTICS			
R _{θJA}	Thermal Resistance, Junction-to-Ambient	350	200	°C/W

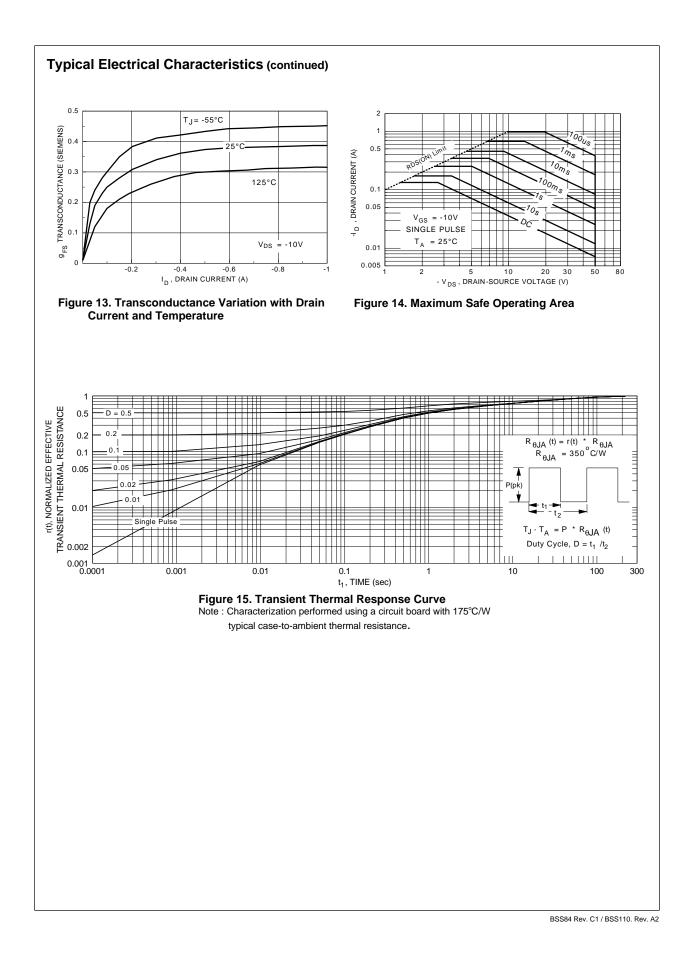
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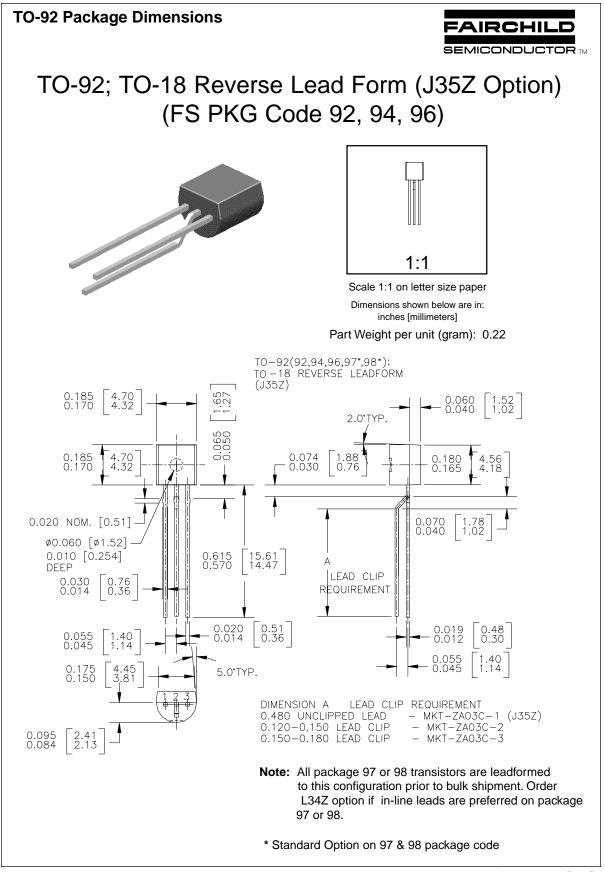
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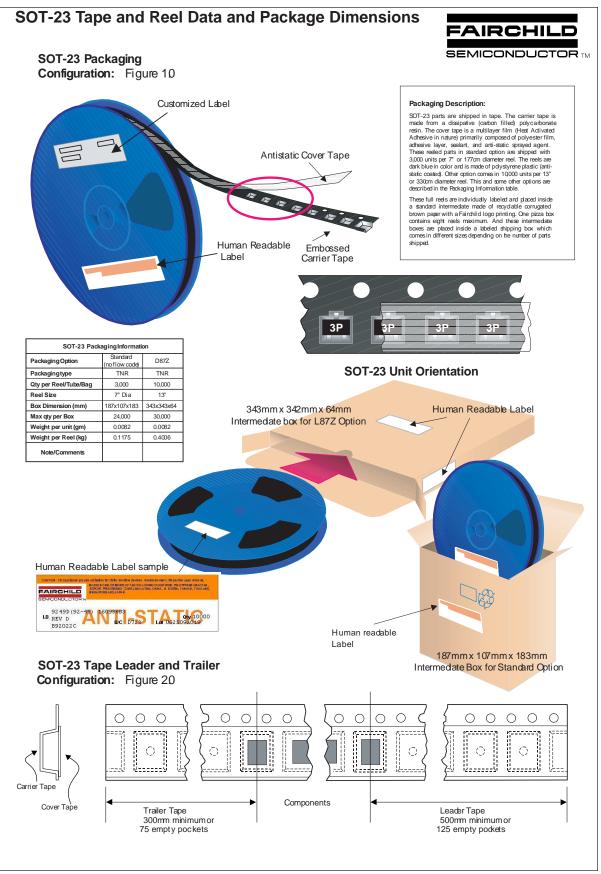
Symbol	Parameter	Conditions		Туре	Min	Тур	Max	Units
OFF CHA	RACTERISTICS							
BV _{DSS}	Drain-Source Breakdown Voltage	$V_{GS} = 0 \text{ V}, I_{D} = -250 \mu\text{A}$		All	-50			V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} = -50 V,		All			-15	μA
		$V_{GS} = 0 V$	T _J = 125°C				-60	μA
		$V_{DS} = -25 \text{ V}, V_{GS} = 0 \text{ V}$					-0.1	μA
GSSR	Gate - Body Leakage, Reverse	$V_{GS} = -20 \text{ V}, V_{DS} = 0 \text{ V}$		All			-10	nA
ON CHA	RACTERISTICS (Note 1)							
V _{GS(th)}	Gate Threshold Voltage	$V_{DS} = V_{GS}$, $I_D = -1 \text{ mA}$		All	-0.8	-1.75	-2	V
R _{DS(ON)}	Static Drain-Source On-Resistance	$V_{GS} = -5V, I_{D} = -0.10 \text{ A}$		BSS84		3.2	10	Ω
		$V_{GS} = -10 \text{ V}, I_{D} = -0.17 \text{ A}$		BSS110		2.2	10	1
9 _{FS}	Forward Transconductance	$V_{DS} = -25 \text{ V}, I_{D} = -0.10 \text{ A}$		BSS84	0.05	0.27		S
		$V_{DS} = -10 \text{ V}, \text{ I}_{D} = -0.17 \text{ A}$			0.05	0.29		
DYNAMIC	CHARACTERISTICS							
C _{iss}	Input Capacitance	$V_{DS} = -25 V, V_{GS} = 0 V,$ f = 1.0 MHz	BSS84		37	45	pF	
		f = 1.0 MHz		BSS110		37		40
C _{oss}	Output Capacitance			All		16	25	pF
C _{rss}	Reverse Transfer Capacitance			All		5	12	pF
SWITCHI	NG CHARACTERISTICS (Note 1)	÷						
t _{D(on)}	Turn - On Delay Time	$V_{\text{DD}} = -30 \text{ V}, \text{ I}_{\text{D}} = -0.27 \text{ A},$ $V_{\text{GS}} = -10 \text{ V}, \text{ R}_{\text{GEN}} = 50 \Omega$		All			12	nS
t,	Turn - On Rise Time			All			50	nS
t _{D(off)}	Turn - Off Delay Time			All			10	nS
<u>.</u>	Turn - Off Fall Time			All			25	nS
T DRAIN-SC	UURCE DIODE CHARACTERISTICS							
I _s	Continuous Source Diode Current		BSS84			-0.13	Α	
			BSS110			-0.17		
I _{SM}	Maximum Pulsed Source Diode Current (Note 1)		BSS84			-0.52	A	
			BSS110			-0.68		
V _{SD}	Drain-Source Diode Forward Voltage	$V_{GS} = 0 V, I_{S} = -0.26 A$ (Note 1)		BSS84		-0.95	-1.2	V
		$V_{GS} = 0 \text{ V}, \text{ I}_{S} = -0.34 \text{ A}$ (Note 1)		BSS110		-1	-1.2	1



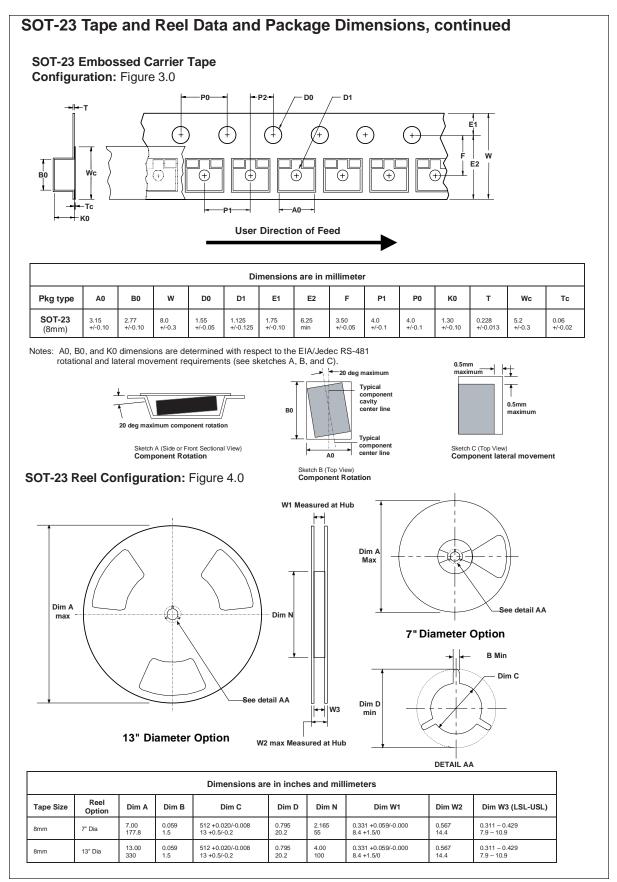




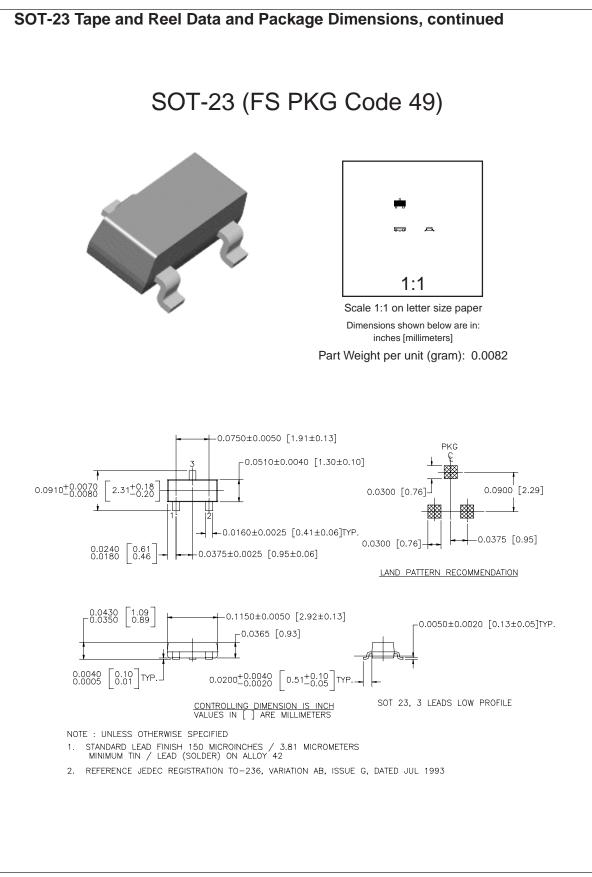




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